



20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BVDSS	R _{DS(ON)} Max	I _D Max T _A = +25°C
	45mΩ @ V _{GS} = 4.5V	4.9A
20V	65mΩ @ V _{GS} = 2.5V	4.1A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The ZXMN2F30FHQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

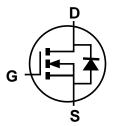
- LED lighting
- Charging applications in portable equipment
- DC-DC converters
- Motor controls

Mechanical Data

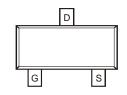
- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish —Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)



Top View



Internal Schematic



Top View

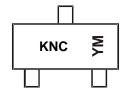
Ordering Information (Note 4)

Ordereble Best Number	Poekere	Packing			
Orderable Part Number	Package	Qty.	Carrier		
ZXMN2F30FHQTA	SOT23	3,000	Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



KNC = Product Type Marking Code YM = Date Code Marking Y or Y = Year (ex: M = 2025) M = Month (ex: 9 = September)

Date Code Key

Year	2016	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	D	-	М	N	Р	R	S	T	U	V	W	Х
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Characteristic		Symbol	Value	Units	
Drain-Source Voltage		VDSS	20	V	
Gate-Source Voltage		V_{GSS}	±12	V	
Continuous Drain Current (Note 6) $V_{GS} = 4.5V$ Steady $T_{A} = +25^{\circ}C$ $T_{A} = +70^{\circ}C$			ΙD	4.9 4.0	А
Maximum Continuous Body Diode Forward Curre	ent (Note 6)	Is	1.6	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle =	1%)		IDM	22.6	Α

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P_D	0.96	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	131	°C/W
Total Power Dissipation (Note 6)		PD	1.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	89	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

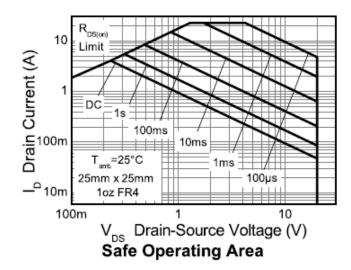
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$	IDSS	I	_	1	μΑ	$V_{DS} = 20V$, $V_{GS} = 0V$
Gate-Source Leakage	Igss		_	±100	nA	$V_{GS} = \pm 12V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	Vgs(TH)	0.6	0.9	1.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
Static Drain-Source On-Resistance	D-s/s/		_	45	mΩ	$V_{GS} = 4.5V, I_{D} = 2.5A$
Static Dialii-Source Off-Nesistance	R _{DS(ON)}		_	65	11122	$V_{GS} = 2.5V, I_{D} = 2.0A$
Diode Forward Voltage	VsD		0.75	1.2	V	Vgs = 0V, Is = 1.25A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}		452	_	рF	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Output Capacitance	Coss	I	102	_	рF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}		58	_	pF	1 = 1.000112
Total Gate Charge	Qg		4.8	_	nC	
Gate-Source Charge	Qgs		1	_	nC	V _{DS} = 10V, V _{GS} = 4.5V, I _D = 3.5A
Gate-Drain Charge	Q _{gd}	I	1.2	_	nC	
Turn-On Delay Time	td(ON)		2.9	_	ns	
Turn-On Rise Time	t _R	_	5.6	_	ns	V _{DS} = 10V, V _{GS} = 4.5V,
Turn-Off Delay Time	t _{D(OFF)}		19.4	_	ns	$R_G = 6\Omega$, $I_D = 1A$
Turn-Off Fall Time	tF	_	10.2	_	ns	

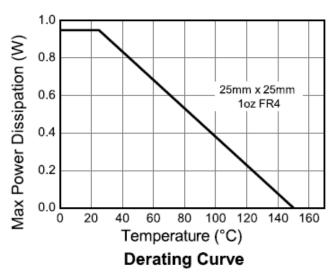
Notes:

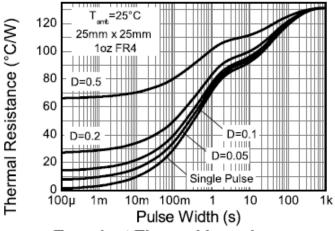
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

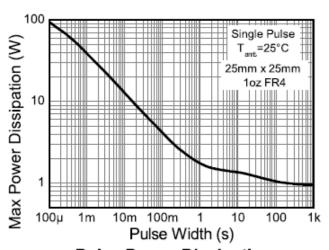


Thermal Characteristics









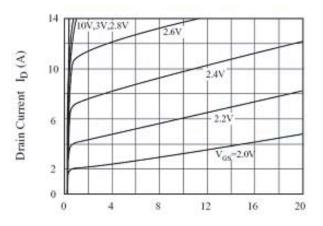
Transient Thermal Impedance

Pulse Power Dissipation



Typical Characteristics





Drain - Source Voltage VDS (V)

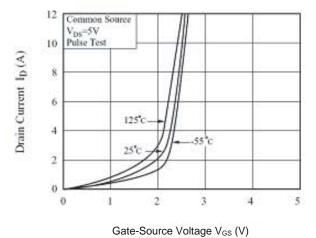
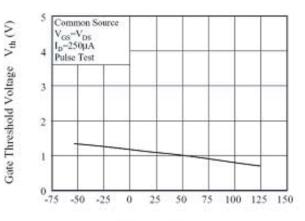
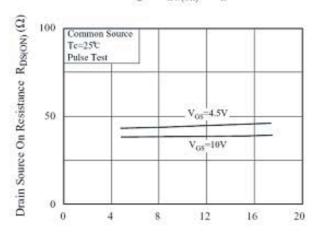


Fig5. Vth-Ti



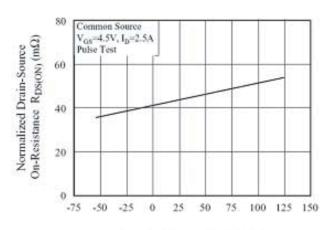
Junction Temperature Ti (*C)

Fig2. RDS(on) - ID



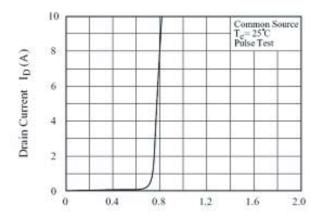
Drain - Current ID (A)

Fig4. RDS(on)-Ti



Junction Temperature T_j (*C)

Fig6. Is-VSDF



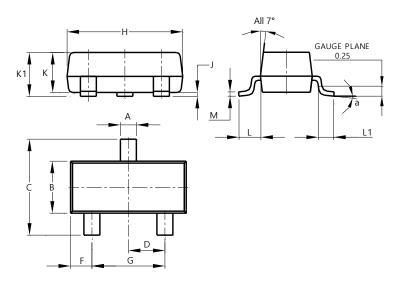
Source - Drain Forward Voltage V_{SDF} (V)



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

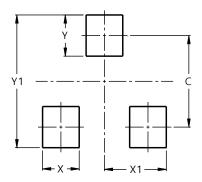


SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Ι	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K 1	0.903	1.10	1.025				
١	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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